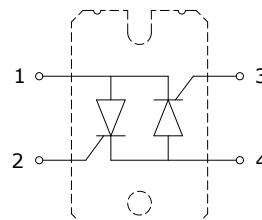


## PRELIMINARY DATASHEET

### Anti-Parallel Silicon Controlled Rectifiers 1600V, 45A in SOT227 Package

- High voltage & high current
- Low on-state voltage
- Suitable for over voltage control, motor control circuit and heating control system
- Pb-free lead finish; RoHS compliant



**MAXIMUM RATINGS**,  $T_c = 25^\circ\text{C}$  unless otherwise noted

| Parameter  | Symbol              | Value       | Units |
|--|---------------------|-------------|-------|
| Average on-state current<br>$T_j = 125^\circ\text{C}$  | $I_{T(\text{AV})}$  | 45          | A     |
| Continuous RMS on-state current as AC switch   | $I_{T(\text{RMS})}$ | 70          |       |
| Non-repetitive surge peak on-state current<br>$T_j = 125^\circ\text{C}$ , $t_p = 10$ ms, applied rated $V_{RRM}$ | $I_{\text{SM}}$     | 630         |       |
| $I_t$ value for fusing<br>$T_j = 125^\circ\text{C}$ , $t_p = 10$ ms, applied rated $V_{RRM}$                     | $I_t$               | 1980        | A·s   |
| Peak gate current<br>$T_j = 125^\circ\text{C}$   | $I_{GM}$            | 2.5         | A     |
| Maximum repetitive peak off-state voltage<br>$I_R = 100\mu\text{A}$  | $V_{DRM}$           | 1600        | V     |
| Maximum repetitive reverse voltage<br>$I_R = 100\mu\text{A}$   | $V_{RRM}$           | 1600        |       |
| Maximum reverse leakage current  | $I_{RRM}$           | 0.2         | mA    |
| Maximum direct leakage current   | $I_{DRM}$           | 0.2         |       |
| Operating junction and storage temperature   | $T_j, T_{stg}$      | -40... +125 | °C    |

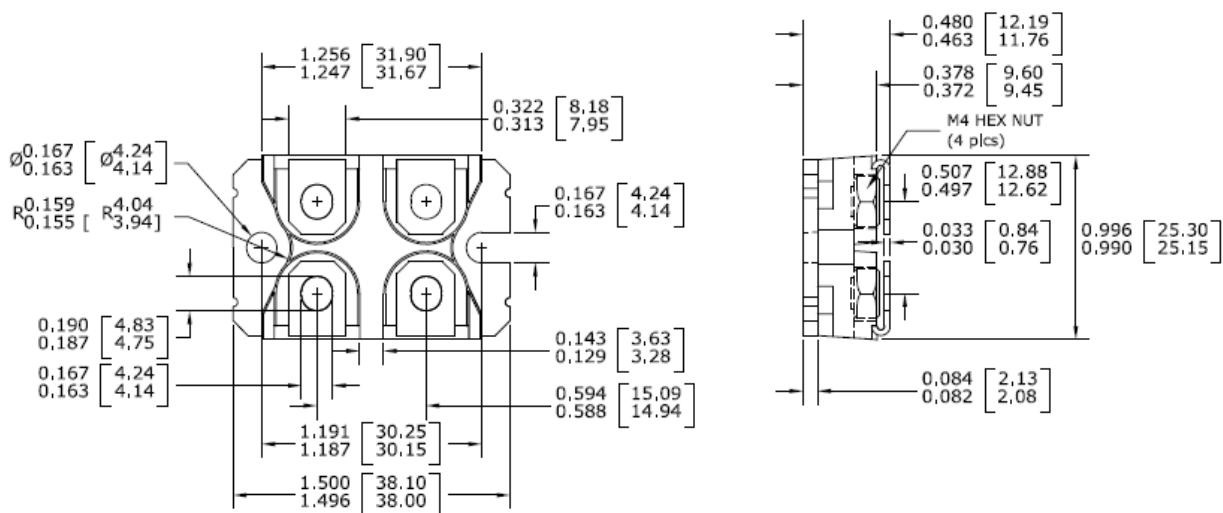
### Thermal Resistance

| Parameter  | Symbol     | Max. Value | Units  |
|--|------------|------------|--------|
| <b>Characteristics</b>   |            |            |        |
| Thermal resistance, junction to case   | $R_{thJC}$ | 1.0        | °C / W |
| Thermal resistance, junction to ambient  | $R_{thJA}$ | 40         |        |
| Isolation voltage, RMS (measured between terminals and mounting base, 50-60 Hz, for 1-2 seconds) | $V_{iso}$  | 3000       | V      |

**Electrical Characteristics**, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

| Parameter                                   | Symbol   | Test Conditions  | Value |      |      | Unit |
|---|----------|--|-------|------|------|------|
|   |          |  | Min.  | Typ. | Max. |      |
| Maximum required DC gate current to trigger | $I_{GT}$ | $\text{Anode Supply} = 6\text{V}$ ,<br>$R_L = 33\Omega$        | -     | -    | 100  | mA   |
| Maximum required DC gate voltage to trigger | $V_{GT}$ |  | -     | -    | 1.5  | V    |
| Maximum holding current                     | $I_H$    | $T_j = 25^\circ\text{C}$ , anode supply 6 V,<br>resistive load | -     | -    | 150  |      |
| Maximum latching current                    | $I_L$    |  | -     | -    | 300  |      |
| Maximum rate of rise of off-state voltage   | $dV/dt$  | $T_j = T_{j\text{max}}$<br>linear to 67% $V_{DRM}$             | -     | -    | 1000 | V/μs |
| Maximum peak on-state voltage               | $V_{TM}$ | 141 A  | -     | -    | 1.9  | V    |
| Maximum peak gate power                     | $P_{GM}$ |  | -     | 10   | -    | W    |

### Package Outline Drawing



CAUTION: These devices are ESD sensitive. Use proper handling procedure.

### Disclaimer

These specifications may not be considered as a guarantee of components characteristics. Components have to be tested depending on intended application as adjustments may be necessary. The use of **iQXPRZ Power Inc.** components in life support appliances and systems are subject to written approval of **iQXPRZ Power Inc.**